



DIM800ECM33-F000

Single Switch IGBT Module

DS5815-1.0 Nov. 2004 (LN23667)

FEATURES

- 10 μ s Short Circuit Withstand
- High Thermal Cycling Capability
- Soft Punch Through Silicon
- Isolated MMC Base-plate with AlN Substrate

APPLICATIONS

- Choppers

The Powerline range of high power modules includes half bridge, chopper, dual, single and bi-directional switch configurations covering voltages from 600V to 3300V and currents up to 3600A.

The DIM800ECM33-F000 is a single switch 3300V, soft punch through, n channel enhancement mode, insulated gate bipolar transistor (IGBT) chopper module. The IGBT has a wide reverse bias safe operating area (RBSOA) plus full 10 μ s short circuit withstand. This device is optimised for traction drives and other applications requiring high thermal cycling capability.

The module incorporates an electrically isolated base plate and low inductance construction enabling circuit designers to optimise circuit layouts and utilise grounded heat sinks for safety.

ORDERING INFORMATION

Order As:

DIM800ECM33-F000

Note: When ordering, please use the whole part number.

KEY PARAMETERS

V_{CES}		3300V
$V_{CE(sat)}$	(typ)	2.8V
I_C	(max)	800A
$I_{C(PK)}$	(max)	1600A

*(measured at the auxiliary terminals)

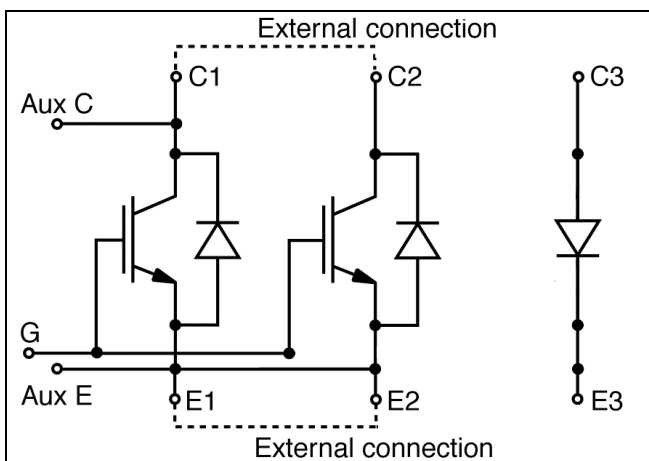


Fig. 1 Single switch circuit diagram

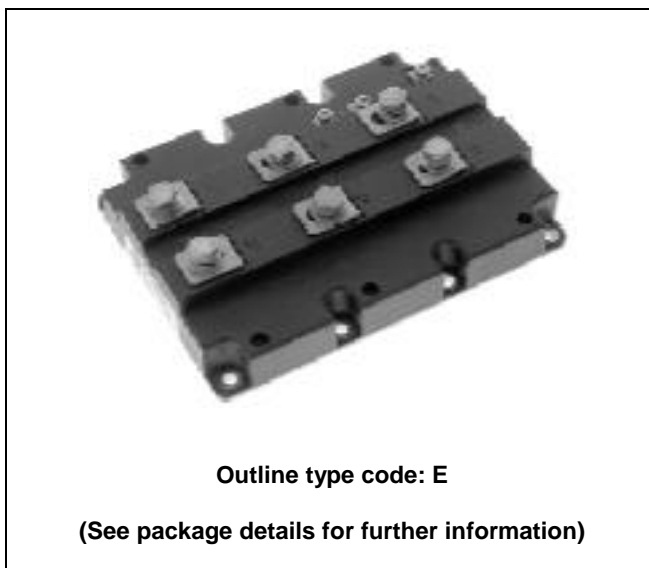


Fig. 2 Electrical connections (not to scale)

ABSOLUTE MAXIMUM RATINGS

Stresses above those listed under ‘Absolute Maximum Ratings’ may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed. Exposure to Absolute Maximum Ratings may affect device reliability.

T_{case} = 25° C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
V _{CES}	Collector-emitter voltage	V _{GE} = 0V	3300	V
V _{GES}	Gate-emitter voltage		±20	V
I _C	Continuous collector current	T _{case} = 90° C	800	A
I _{C(PK)}	Peak collector current	1ms, T _{case} = 115° C	1600	A
P _{max}	Max. transistor power dissipation	T _{case} = 25° C, T _j = 150° C	10.4	kW
I ² t	Diode I ² t value (IGBT arm)	V _R = 0, t _P = 10ms, T _{vj} = 125° C	320	kA ² S
V _{isol}	Isolation voltage – per module	Commoned terminals to base plate. AC RMS, 1 min, 50Hz	6000	V
Q _{PD}	Partial discharge – per module	IEC1287. V ₁ = 3500V, V ₂ = 2600V, 50Hz RMS	10	pC

THERMAL AND MECHANICAL RATINGS

Internal insulation material: AIN
 Baseplate material: AISiC
 Creepage distance: 29mm
 Clearance: 20mm
 CTI (Critical Tracking Index): 175

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$R_{th(j-c)}$	Thermal resistance – transistor both arms	Continuous dissipation – junction to case	-	-	12	° C/kW
$R_{th(j-c)}$	Thermal resistance – diode, C3-E3 and C1-E1 in parallel with C2-E2	Continuous dissipation – junction to case	-	-	24	° C/kW
$R_{th(c-h)}$	Thermal resistance – case to heatsink (per module)	Mounting torque 5Nm (with mounting grease)	-	-	6	° C/kW
T_j	Junction temperature	Transistor	-	-	150	° C
		Diode	-	-	125	° C
T_{stg}	Storage temperature range	-	-40	-	125	° C
-	Screw torque	Mounting – M6	-	-	5	Nm
		Electrical connections – M4	-	-	2	Nm
		Electrical connections – M8	-	-	10	Nm

ELECTRICAL CHARACTERISTICS

$T_{case} = 25^{\circ}C$ unless stated otherwise.

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Units
I _{CES}	Collector cut-off current	V _{GE} = 0V, V _{CE} = V _{CES}		-	-	4	mA
		V _{GE} = 0V, V _{CE} = V _{CES} , T _{case} = 125° C		-	-	60	mA
I _{CES}	Gate leakage current	V _{GE} = ±20V, V _{CE} = 0V		-	-	1	μA
V _{GE(TH)}	Gate threshold voltage	I _C = 80mA, V _{GE} = V _{CE}		5.5	6.5	7.0	V
V _{CE(sat)} [†]	Collector-emitter saturation voltage	V _{GE} = 15V, I _C = 800A		-	2.8		V
		V _{GE} = 15V, I _C = 800A, T _{case} = 125° C		-	3.6	-	V
I _F	Diode forward current	DC		-	800	-	A
I _{FM}	Diode maximum forward current	t _p = 1ms		-	1600	-	A
V _F [†]	Diode forward voltage	I _F = 800A		-	2.9	-	V
		I _F = 800A, T _{case} = 125° C		-	3.0	-	V
C _{ies}	Input capacitance	V _{CE} = 25V, V _{GE} = 0V, f = 1MHz			144	-	nF
C _{res}	Reverse transfer capacitance	V _{CE} = 25V, V _{GE} = 0V, f = 1MHz		-	2.2	-	nF
L _M	Module inductance	-		-	15	-	nH
R _{INT}	Internal transistor resistance	-		-	0.135	-	mΩ
SC _{Data}	Short circuit. I _{sc}	T _j = 125° C, V _{CC} = 2500V, t _p ≤ 10μs, V _{CE(max)} = V _{CES} - L*.di/dt IEC 60747-9	I ₁	-	4000	-	A
			I ₂	-	3700	-	A

Note:

\dagger Measured at the auxiliary terminals

L^* is the circuit inductance + L_M

ELECTRICAL CHARACTERISTICS

$T_{case} = 25^{\circ}C$ unless stated otherwise.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$t_{d(off)}$	Turn-off delay time	$I_C = 800A$ $V_{GE} = \pm 15V$ $V_{CE} = 1800V$ $R_{G(ON)} = 2.7\Omega, R_{G(OFF)} = 3.9\Omega$ $L \sim 100nH$ $C_{ge} = 220nF$	-	2150	-	ns
t_f	Fall time		-	230	-	ns
E_{OFF}	Turn-off energy loss		-	1050	-	mJ
$t_{d(on)}$	Turn-on delay time		-	1300	-	ns
t_r	Rise time		-	275	-	ns
E_{ON}	Turn-on energy loss		-	1250	-	mJ
Q_g	Gate charge		-	20	-	μC
Q_{rr}	Diode reverse recovery charge	$I_F = 800A, V_R = 1800V,$ $dI_F/dt = 4000A/\mu s$	-	320	-	μC
I_{rr}	Diode reverse current		-	670	-	A
E_{REC}	Diode reverse recovery energy		-	300	-	mJ

$T_{case} = 125^{\circ}C$ unless stated otherwise.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$t_{d(off)}$	Turn-off delay time	$I_C = 800A$ $V_{GE} = \pm 15V$ $V_{CE} = 1800V$ $R_{G(ON)} = 2.7\Omega, R_{G(OFF)} = 3.9\Omega$ $L \sim 100nH$ $C_{ge} = 220nF$	-	2200	-	ns
t_f	Fall time		-	240	-	ns
E_{OFF}	Turn-off energy loss		-	1200	-	mJ
$t_{d(on)}$	Turn-on delay time		-	1200	-	ns
t_r	Rise time		-	315	-	ns
E_{ON}	Turn-on energy loss		-	1750	-	mJ
Q_{rr}	Diode reverse recovery charge	$I_F = 800A, V_R = 1800V,$ $dI_F/dt = 4000A/\mu s$	-	600	-	μC
I_{rr}	Diode reverse current		-	800	-	A
E_{REC}	Diode reverse recovery energy		-	600	-	mJ

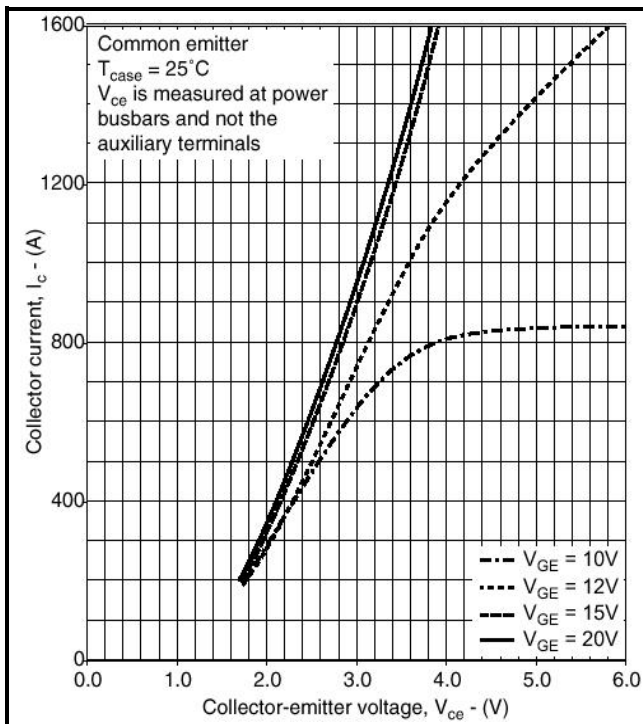


Fig.3 Typical output characteristics

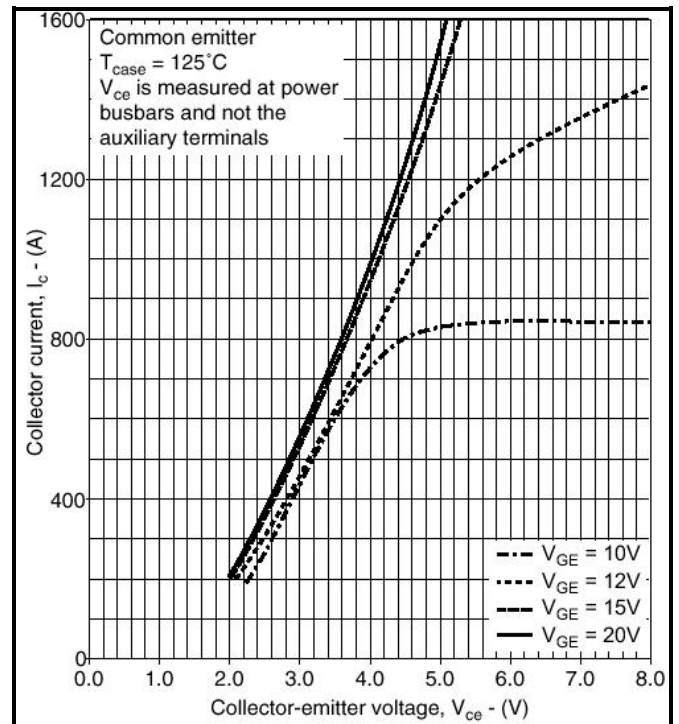


Fig.4 Typical output characteristics

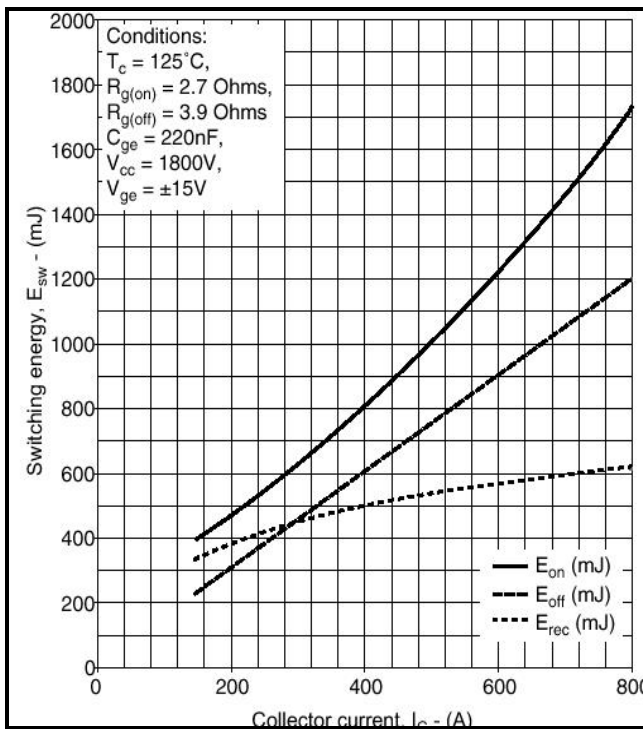


Fig.5 Typical switching energy vs collector current

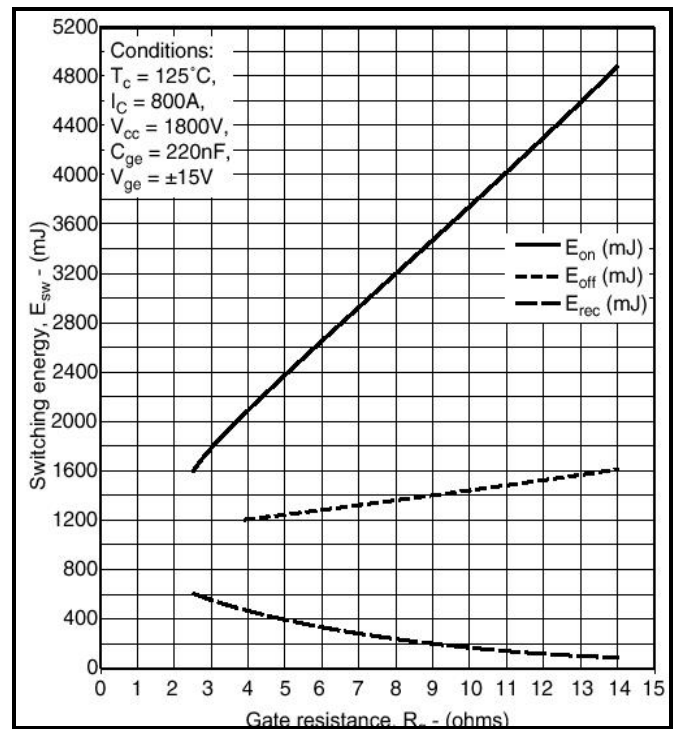


Fig.6 Typical switching energy vs gate resistance

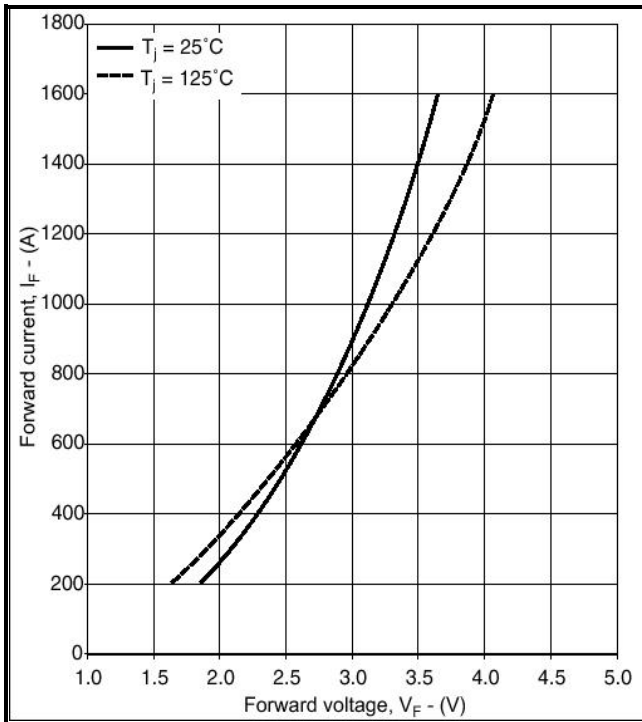


Fig.7 Diode typical forward characteristics

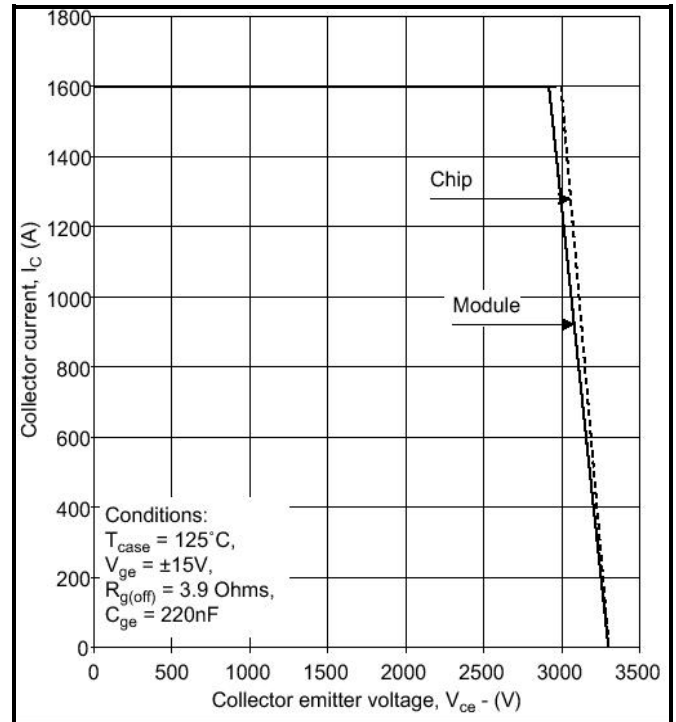


Fig.8 Reverse bias safe operating area

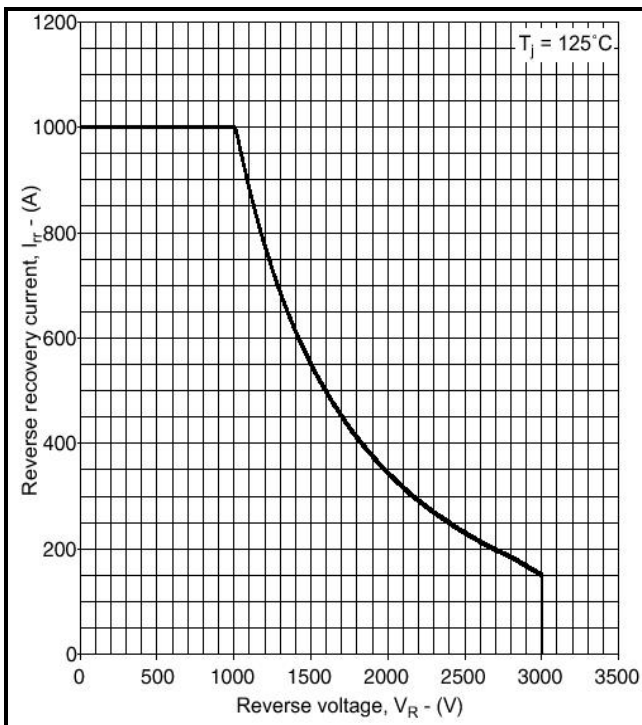


Fig.9 Diode reverse bias safe operating area

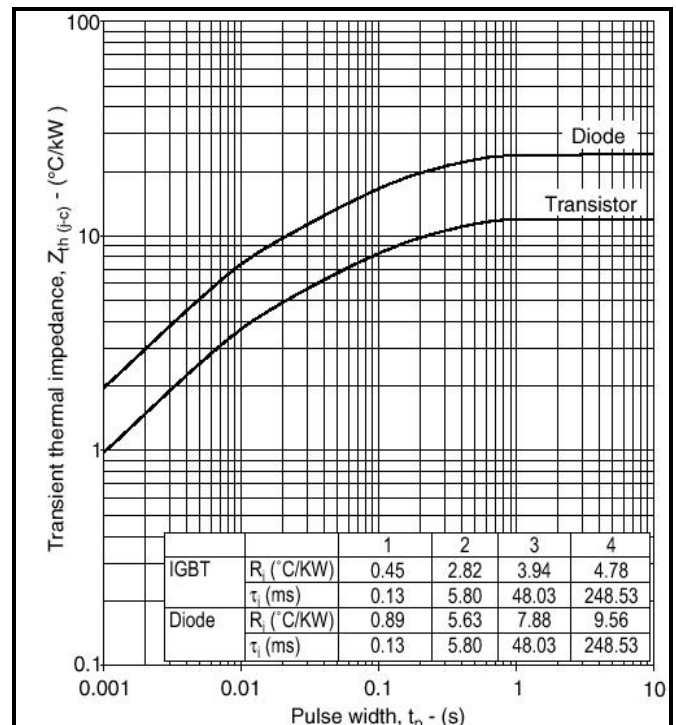
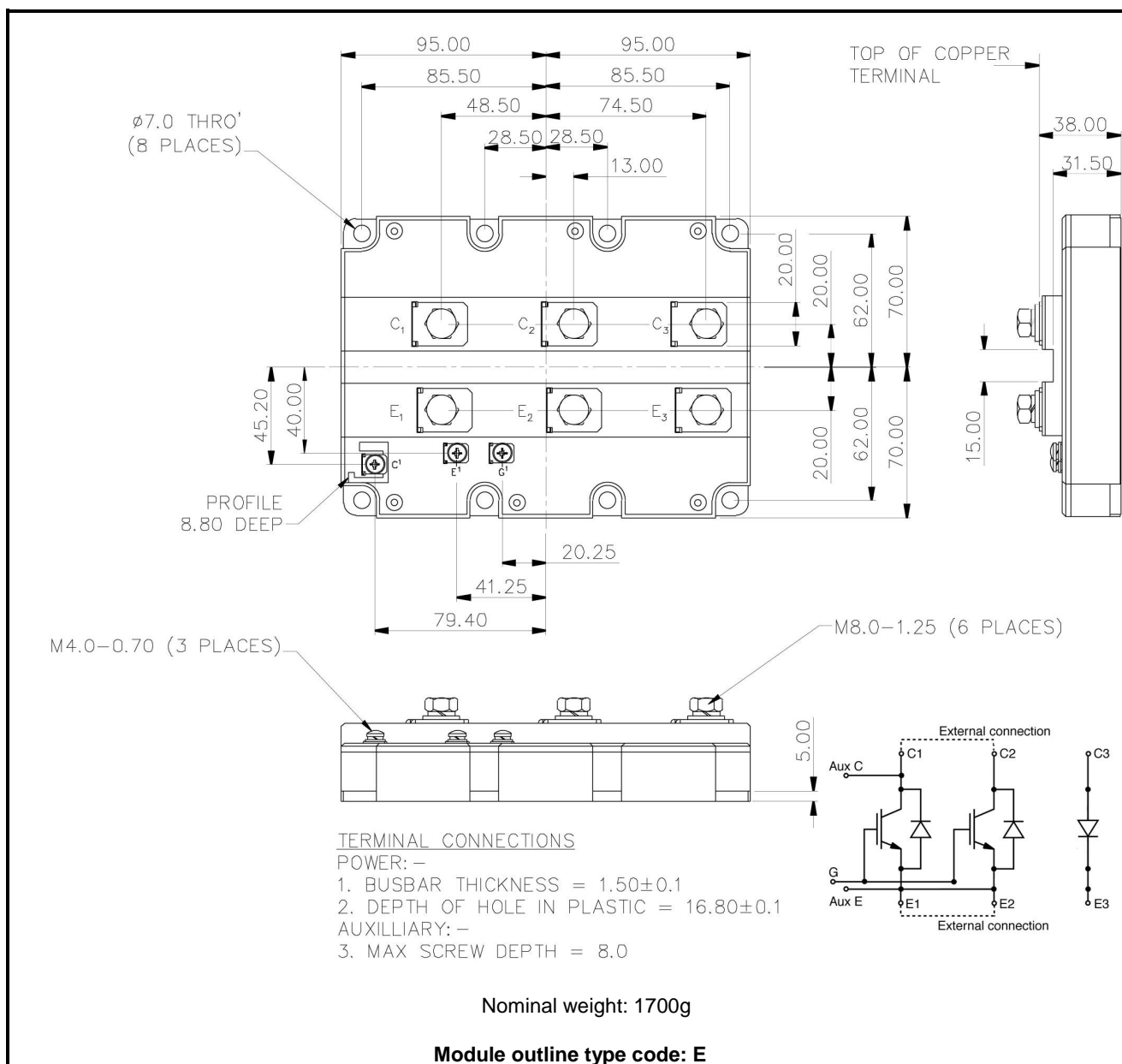


Fig.10 Transient thermal impedance

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DO NOT SCALE.



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Using the latest CAD methods our team of design and applications engineers aim to provide the Power Assembly Complete Solution (PACs).

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The Power Assembly group has its own proprietary range of extruded aluminium heatsinks which have been designed to optimise the performance of Dynex semiconductors. Data with respect to air natural, forced air and liquid cooling (with flow rates) is available on request.

For further information on device clamps, heatsinks and assemblies, please contact your nearest sales representative or Customer Services.



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